



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Ryu et al.

Group Art Unit: 2811

Serial No.: 09/911,995

Confirmation No.: 5240

Filed: July 24, 2001

For: SILICON CARBIDE POWER METAL-OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS HAVING A SHORTING CHANNEL AND METHODS OF FABRICATING SILICON CARBIDE METAL-OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS HAVING A SHORTING CHANNEL

Date: October 22, 2001

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Rayton

Commissioner for Patents
Washington, DC 20231

INFORMATION DISCLOSURE STATEMENT
CITATION UNDER 37 C.F.R. § 1.97

Sir:

Attached is a list of documents on form PTO-1449 together with a copy of each identified document. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.97 and Section 609 of the MPEP.

No item of information contained in this Statement was cited from a foreign patent office in a counterpart foreign application.

Respectfully submitted,

Timothy J. O'Sullivan
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20792

PATENT TRADEMARK OFFICE

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231 on October 22, 2001.

Traci A. Brown

Date of Signature: October 22, 2001

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